

IRGB420UD2

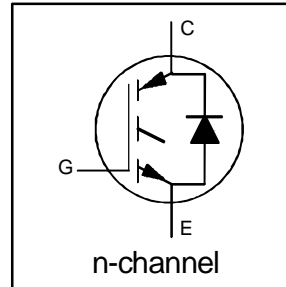
INSULATED GATE BIPOLAR TRANSISTOR
WITH ULTRAFAST SOFT RECOVERY

UltraFast CoPack IGBT

DIODE

Features

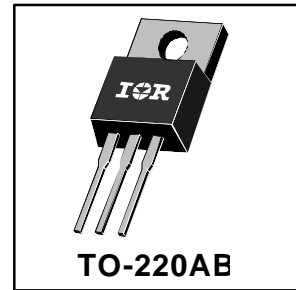
- Switching-loss rating includes all "tail" losses
- HEXFRED™ soft ultrafast diodes
- Optimized for high operating frequency (over 5kHz)
See Fig. 1 for Current vs. Frequency curve



| |
|------------------------------|
| $V_{CES} = 500V$ |
| $V_{CE(sat)} \leq 2.9V$ |
| @ $V_{GE} = 15V, I_C = 7.5A$ |

Description

Co-packaged IGBTs are a natural extension of International Rectifier's well known IGBT line. They provide the convenience of an IGBT and an ultrafast recovery diode in one package, resulting in substantial benefits to a host of high-voltage, high-current, motor control, UPS and power supply applications.



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---------------------------|--|---------------------|-------|
| V_{CES} | Collector-to-Emitter Voltage | 500 | V |
| $I_C @ T_C = 25^\circ C$ | Continuous Collector Current | 14 | A |
| $I_C @ T_C = 100^\circ C$ | Continuous Collector Current | 7.5 | |
| I_{CM} | Pulsed Collector Current ① | 28 | |
| I_{LM} | Clamped Inductive Load Current ② | 28 | |
| $I_F @ T_C = 100^\circ C$ | Diode Continuous Forward Current | 7.0 | |
| I_{FM} | Diode Maximum Forward Current | 28 | |
| V_{GE} | Gate-to-Emitter Voltage | ± 20 | V |
| $P_D @ T_C = 25^\circ C$ | Maximum Power Dissipation | 60 | W |
| $P_D @ T_C = 100^\circ C$ | Maximum Power Dissipation | 24 | |
| T_J | Operating Junction and Storage Temperature Range | -55 to +150 | °C |
| T_{STG} | | | |
| | | | |
| | Mounting Torque, 6-32 or M3 Screw. | 10 lbf•in (1.1 N•m) | |

Thermal Resistance

| | Parameter | Min. | Typ. | Max. | Units |
|-----------------|---|------|----------|------|--------|
| $R_{\theta JC}$ | Junction-to-Case - IGBT | — | — | 2.1 | °C/W |
| $R_{\theta JC}$ | Junction-to-Case - Diode | — | — | 3.5 | |
| $R_{\theta CS}$ | Case-to-Sink, flat, greased surface | — | 0.50 | — | |
| $R_{\theta JA}$ | Junction-to-Ambient, typical socket mount | — | — | 80 | |
| Wt | Weight | — | 2 (0.07) | — | g (oz) |

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---------------------------------|--|------|------|-----------|---------|---|
| $V_{(BR)CES}$ | Collector-to-Emitter Breakdown Voltage ③ | 500 | — | — | V | $V_{GE} = 0V, I_C = 250\mu A$ |
| $\Delta V_{(BR)CES}/\Delta T_J$ | Temp. Coeff. of Breakdown Voltage | — | 0.47 | — | V/°C | $V_{GE} = 0V, I_C = 1.0mA$ |
| $V_{CE(on)}$ | Collector-to-Emitter Saturation Voltage | — | 2.4 | 2.9 | V | $I_C = 7.5A, V_{GE} = 15V$ See Fig. 2, 5 |
| | | — | 3.1 | — | | |
| | | — | 2.7 | — | | |
| $V_{GE(th)}$ | Gate Threshold Voltage | 3.0 | — | 5.5 | | $V_{CE} = V_{GE}, I_C = 250\mu A$ |
| $\Delta V_{GE(th)}/\Delta T_J$ | Temp. Coeff. of Threshold Voltage | — | -10 | — | mV/°C | $V_{CE} = V_{GE}, I_C = 250\mu A$ |
| g_{fe} | Forward Transconductance ④ | 1.2 | 2.0 | — | S | $V_{CE} = 100V, I_C = 7.5A$ |
| I_{CES} | Zero Gate Voltage Collector Current | — | — | 250 | μA | $V_{GE} = 0V, V_{CE} = 500V$ $V_{GE} = 0V, V_{CE} = 500V, T_J = 150^\circ\text{C}$ |
| | | — | — | 1700 | | |
| V_{FM} | Diode Forward Voltage Drop | — | 1.4 | 1.7 | V | $I_C = 8.0A$ See Fig. 13 $I_C = 8.0A, T_J = 150^\circ\text{C}$ |
| | | — | 1.3 | 1.6 | | |
| I_{GES} | Gate-to-Emitter Leakage Current | — | — | ± 100 | nA | $V_{GE} = \pm 20V$ |

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|------------------|--|------|------|------|------------|---|
| Q_g | Total Gate Charge (turn-on) | — | 15 | 23 | nC | $I_C = 7.5A$ $V_{CC} = 400V$ See Fig. 8 |
| Q_{ge} | Gate - Emitter Charge (turn-on) | — | 3.7 | 5.6 | | |
| Q_{gc} | Gate - Collector Charge (turn-on) | — | 6.5 | 9.8 | | |
| $t_{d(on)}$ | Turn-On Delay Time | — | 65 | — | ns | $T_J = 25^\circ\text{C}$ $I_C = 7.5A, V_{CC} = 400V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 11, 18 |
| t_r | Rise Time | — | 44 | — | | |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 140 | 210 | | |
| t_f | Fall Time | — | 110 | 160 | | |
| E_{on} | Turn-On Switching Loss | — | 0.25 | — | mJ | See Fig. 9, 10, 11, 18 |
| E_{off} | Turn-Off Switching Loss | — | 0.25 | — | | |
| E_{ts} | Total Switching Loss | — | 0.50 | 0.80 | | |
| $t_{d(on)}$ | Turn-On Delay Time | — | 60 | — | ns | $T_J = 150^\circ\text{C}$, See Fig. 9, 10, 11, 18 $I_C = 7.5A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" and diode reverse recovery. |
| t_r | Rise Time | — | 44 | — | | |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 230 | — | | |
| t_f | Fall Time | — | 220 | — | | |
| E_{ts} | Total Switching Loss | — | 0.8 | — | mJ | |
| L_E | Internal Emitter Inductance | — | 7.5 | — | nH | Measured 5mm from package |
| C_{ies} | Input Capacitance | — | 330 | — | pF | $V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$ |
| C_{oes} | Output Capacitance | — | 47 | — | | |
| C_{res} | Reverse Transfer Capacitance | — | 5.9 | — | | |
| t_{rr} | Diode Reverse Recovery Time | — | 37 | 55 | ns | $T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$ |
| | | — | 55 | 90 | | |
| I_{rr} | Diode Peak Reverse Recovery Current | — | 3.5 | 5.0 | A | $T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$ |
| | | — | 4.5 | 8.0 | | |
| Q_{rr} | Diode Reverse Recovery Charge | — | 65 | 138 | nC | $T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$ |
| | | — | 124 | 360 | | |
| $di_{(rec)M}/dt$ | Diode Peak Rate of Fall of Recovery During t_b | — | 240 | — | A/ μs | $T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$ |
| | | — | 210 | — | | |

Notes:

① Repetitive rating; $V_{GE}=20V$, pulse width limited by max. junction temperature. (See fig. 20)

② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=50\Omega$, (See fig. 19)

④ Pulse width 5.0 μs , single shot.

③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.

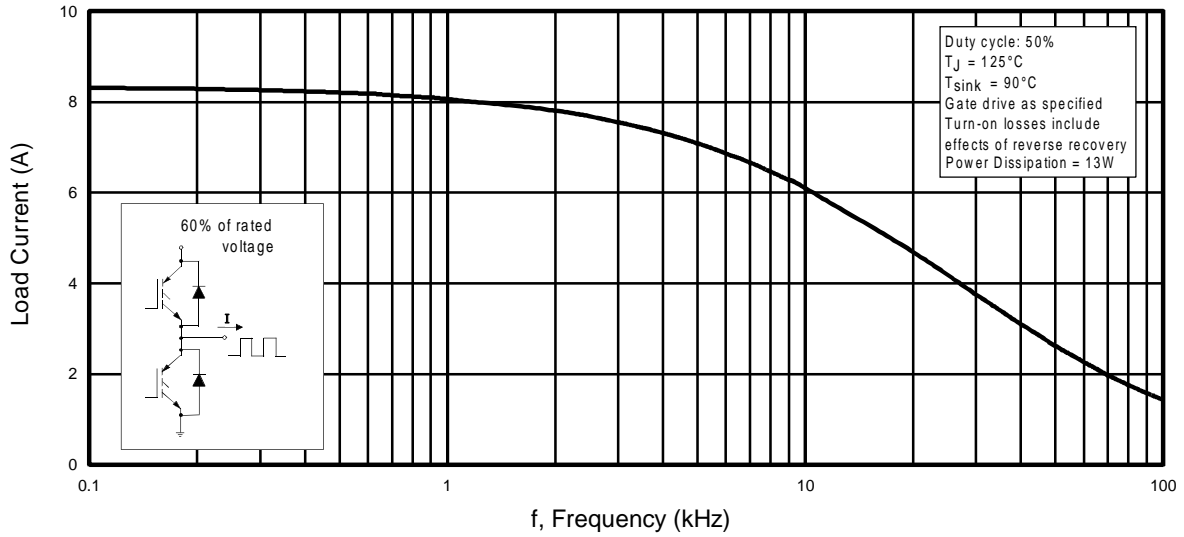


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

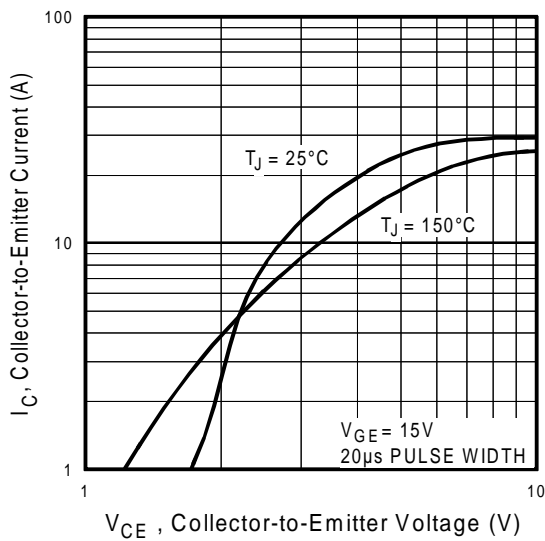


Fig. 2 - Typical Output Characteristics

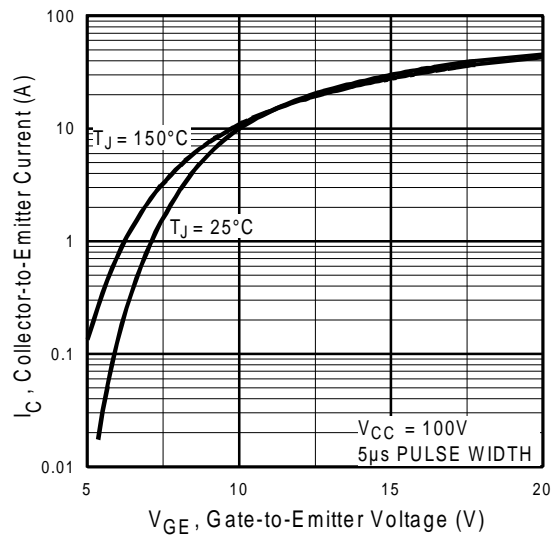


Fig. 3 - Typical Transfer Characteristics

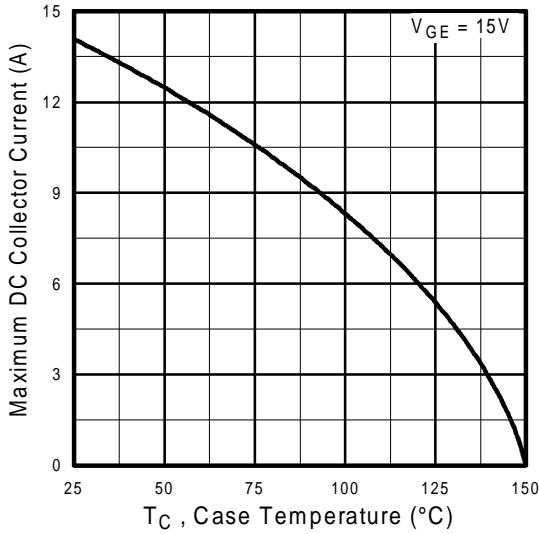


Fig. 4 - Maximum Collector Current vs. Case Temperature

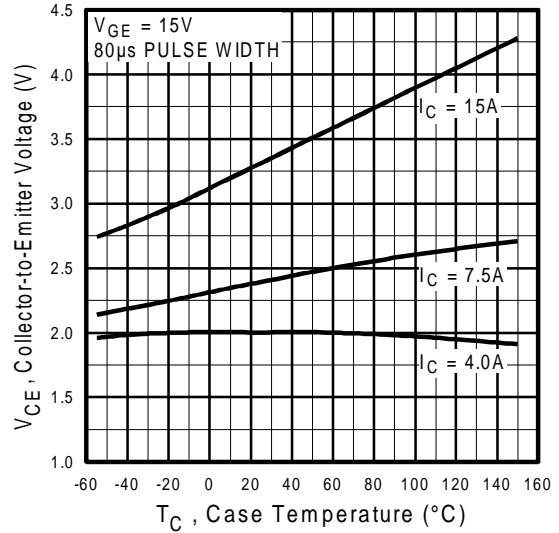


Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

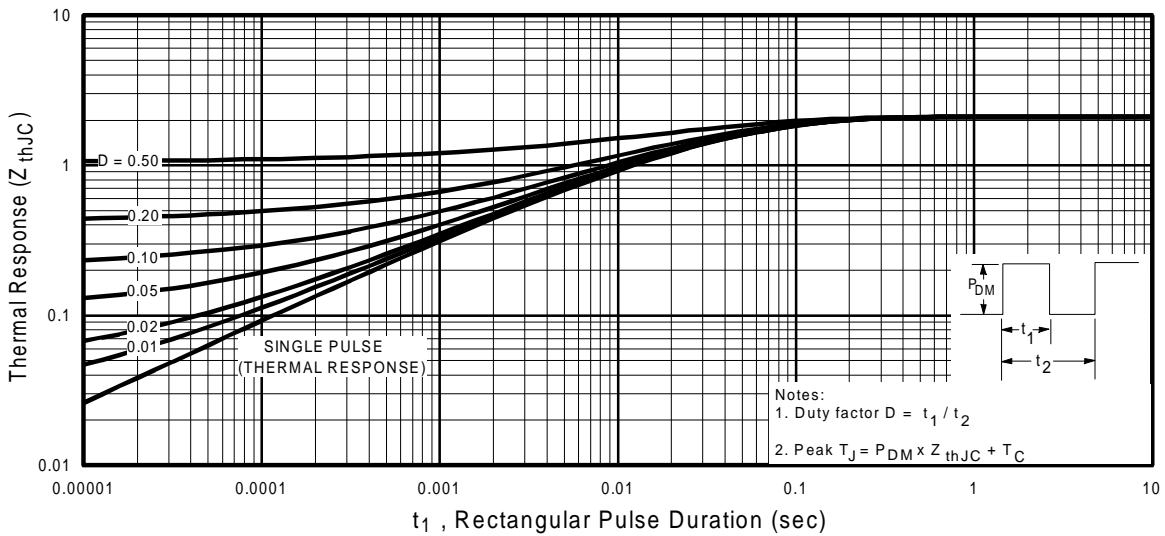


Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

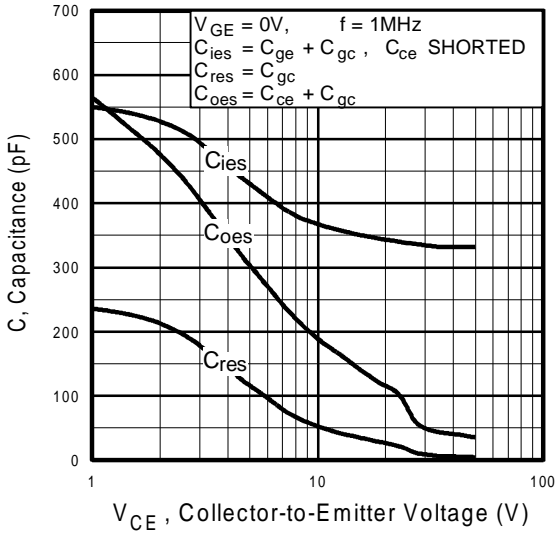


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

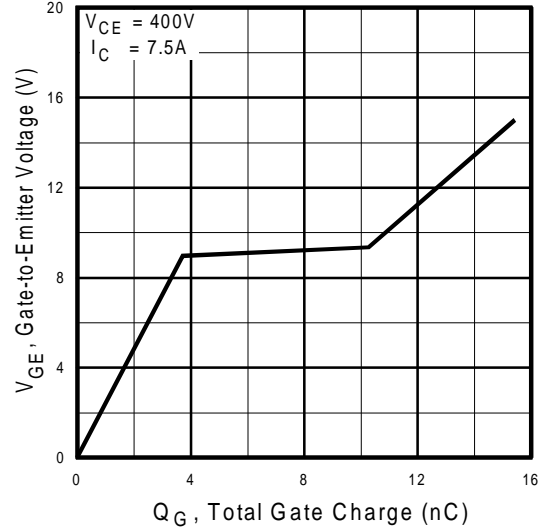


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

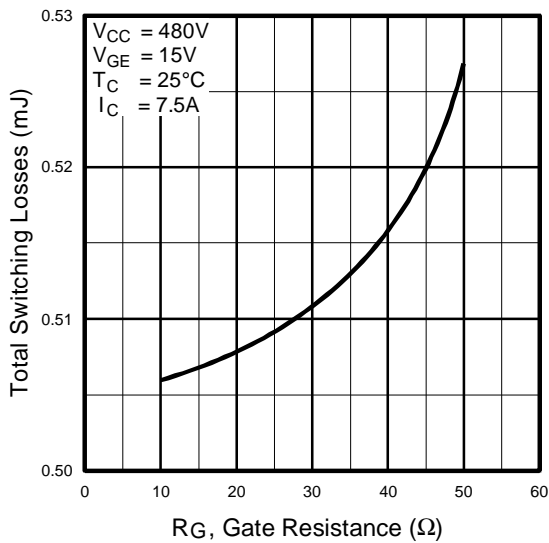


Fig. 9 - Typical Switching Losses vs. Gate Resistance

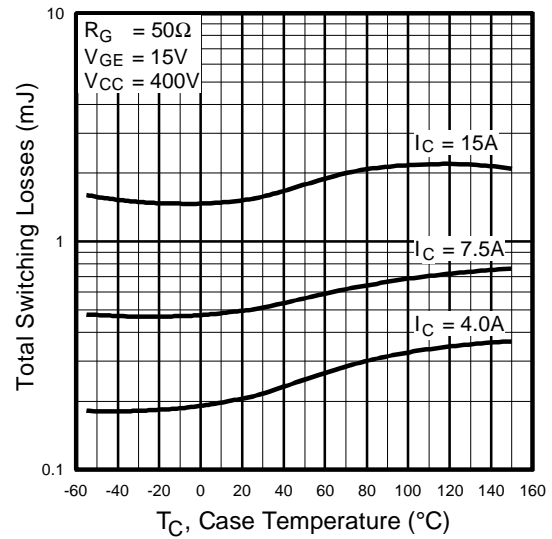


Fig. 10 - Typical Switching Losses vs. Case Temperature

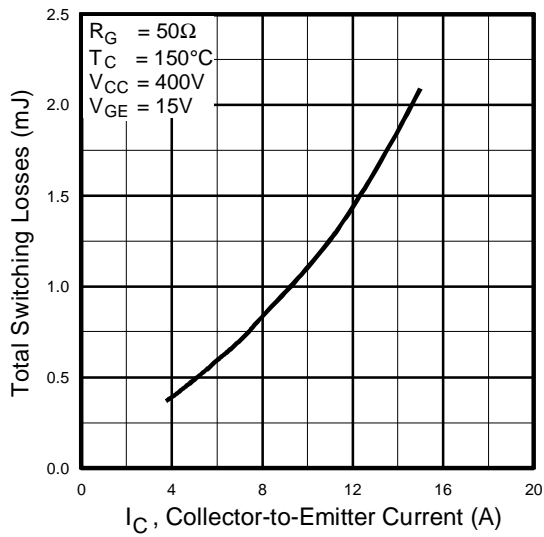


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

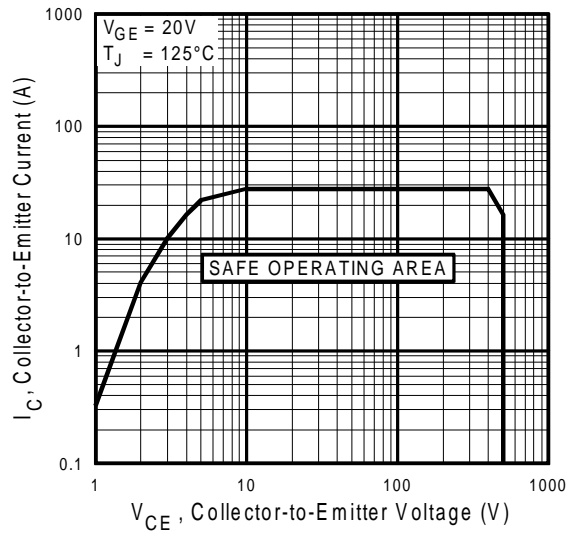


Fig. 12 - Turn-Off SOA

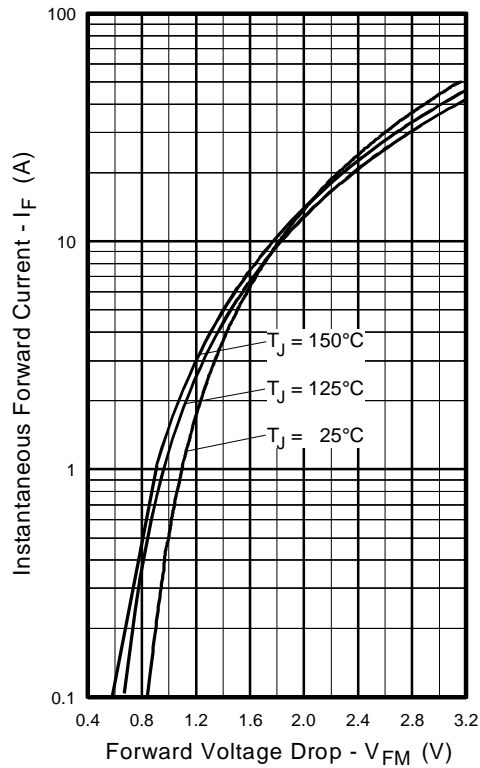


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

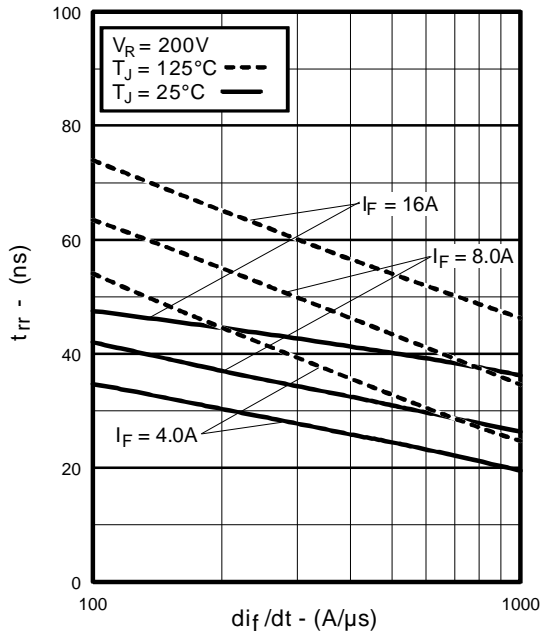


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

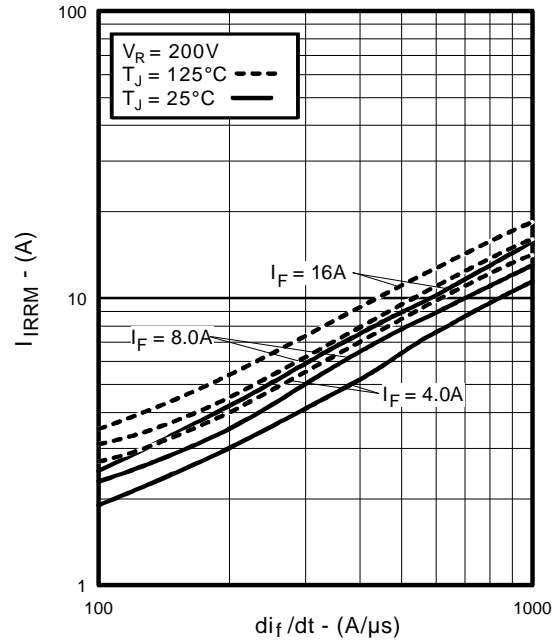


Fig. 15 - Typical Recovery Current vs. di_f/dt

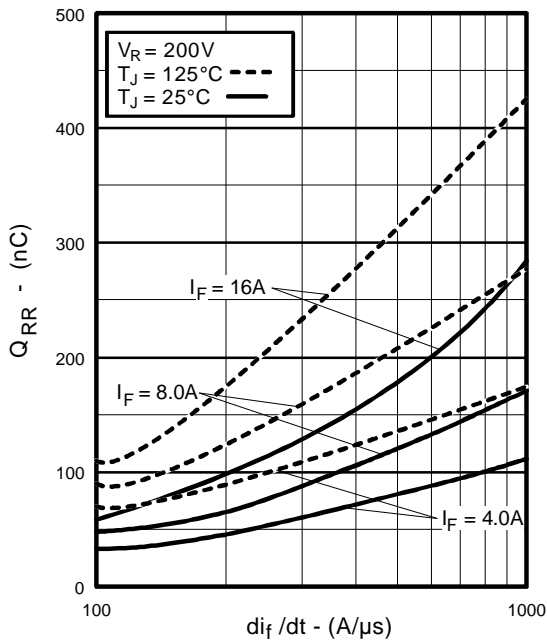


Fig. 16 - Typical Stored Charge vs. di_f/dt

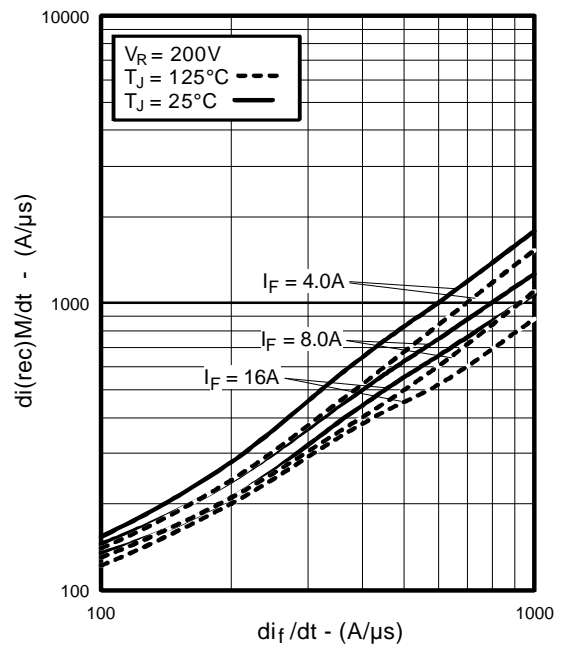


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

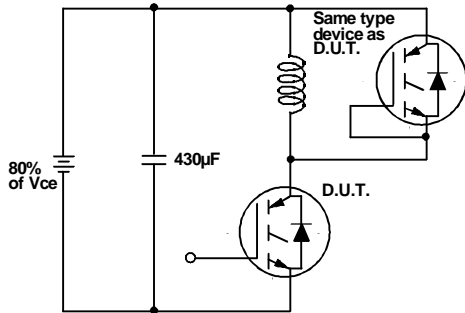


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

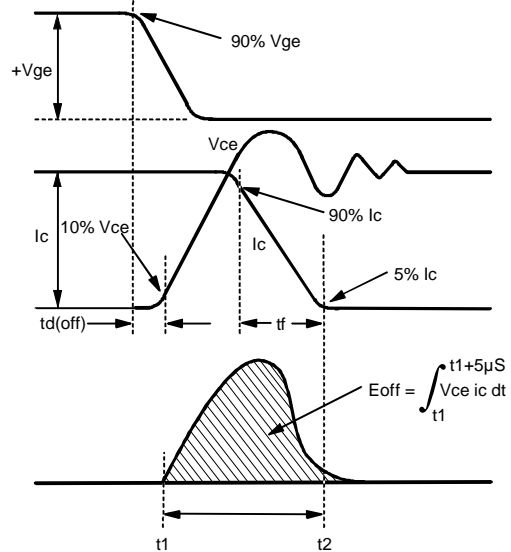


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

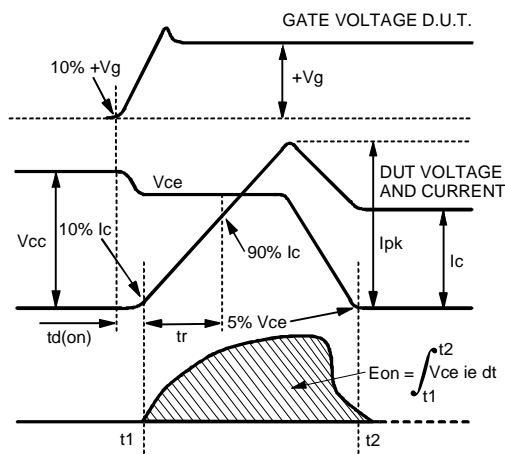


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

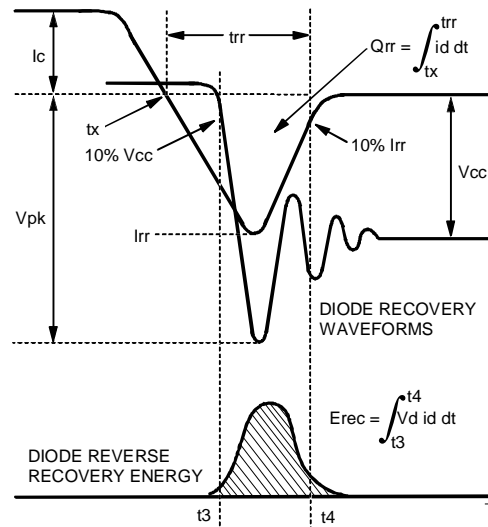


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

Refer to Section D for the following:

Appendix B: Section D - page D-4

Fig. 18e - Macro Waveforms for Test Circuit of Fig. 18a

Fig. 19 - Clamped Inductive Load Test Circuit

Fig. 20 - Pulsed Collector Current Test Circuit